

RESPONSE TO OFFICE ACTION
Serial No. 10/624,763
Page 2 of 9

IN THE CLAIMS

1. (Currently Amended) A method of defining a feature on a substrate, comprising:
 - (a) providing a substrate having a multilayer stack formed thereon;
 - (b) forming a first mask ~~through~~ by patterning one or more layers of the multilayer stack;
 - (c) forming a conformal second mask on one or more sidewalls of the first mask;
 - (d) etching one or more layers of the multilayer stack ~~to the substrate surface~~ using the second mask to form an opening in the multilayer stack;
 - (e) filling the opening ~~formed in the multilayer stack~~ with one or more material layers; and
 - (f) removing the multilayer stack from the substrate leaving thereon a feature formed of the one or more material layers.
2. (Original) The method of claim 1 wherein step (b) further comprises:
 - (b1) forming a photoresist pattern on the multilayer stack;
 - (b2) transferring the photoresist pattern through one or more layers of the multilayer stack; and
 - (b3) removing the photoresist pattern from the multilayer stack.
3. (Original) The method of claim 1 wherein the first mask comprises at least one of a dielectric antireflective coating (DARC) and an amorphous carbon layer.
4. (Currently Amended) The method of claim 1 wherein step (c) further comprises:
 - (c1) depositing a second mask layer conformably on the first mask; and
 - (c2) etching portions of the second mask layer on horizontal surfaces of the substrate ~~leaving the second mask layer on one or more sidewalls of the first mask.~~

RESPONSE TO OFFICE ACTION
Serial No. 10/624,763
Page 3 of 9

5. (Original) The method of claim 1 wherein the second mask comprises a material selected from the group consisting of silicon dioxide (SiO_2) and silicon nitride (Si_3N_4).
6. (Original) The method of claim 1 wherein the one or more material layers filling the opening formed in the multilayer stack comprise polysilicon.
7. (Currently Amended) A method of fabricating a notch gate structure of a field effect transistor comprising:
- (a) providing a substrate having a multilayer stack formed on a gate dielectric layer;
 - (b) forming a first mask ~~through~~ by patterning one or more layers of the multilayer stack;
 - (c) forming a conformal second mask on one or more sidewalls of the first mask;
 - (d) etching one or more layers of the multilayer stack to ~~the surface of~~ the gate dielectric layer using the second mask to form a notch gate opening in the multilayer stack;
 - (e) filling the notch gate opening ~~formed in the multilayer stack~~ with one or more material layers; and
 - (f) removing the multilayer stack from the substrate leaving thereon a notch gate electrode formed on the gate dielectric layer.
8. (Original) The method of claim 7 wherein step (b) further comprises:
- (b1) forming a photoresist pattern on the multilayer stack;
 - (b2) transferring the photoresist pattern through one or more layers of the multilayer stack; and
 - (b3) removing the photoresist pattern from the multilayer stack.

RESPONSE TO OFFICE ACTION
Serial No. 10/624,763
Page 4 of 9

9. (Original) The method of claim 7 wherein the first mask comprises at least one of a dielectric antireflective coating (DARC) and an amorphous carbon layer.
10. (Currently Amended) The method of claim 7 wherein step (c) further comprises:
(c1) depositing a second mask layer conformably on the first mask; and
(c2) etching portions of the second mask layer on horizontal surfaces of the substrate ~~leaving the second mask layer on one or more sidewalls of the first mask.~~
11. (Original) The method of claim 7 wherein the second mask comprises a material selected from the group consisting of silicon dioxide (SiO_2) and silicon nitride (Si_3N_4).
12. (Original) The method of claim 7 wherein the one or more material layers filling the notch gate opening formed in the multilayer stack comprise polysilicon.
13. (Currently Amended) A method of fabricating a field effect transistor, comprising:
(a) providing a substrate having a multilayer stack formed on a gate dielectric layer;
(b) forming a first mask through by patterning one or more layers of the multilayer stack;
(c) forming a conformal second mask on one or more sidewalls of the first mask;
(d) etching one or more layers of the multilayer stack to ~~the surface of~~ the gate dielectric layer using the second mask to form a notch gate opening in the multilayer stack;
(e) filling the notch gate opening ~~formed in the multilayer stack~~ with one or more material layers; and
(d) removing the multilayer stack from the substrate leaving thereon a notch gate electrode formed on the gate dielectric layer.

RESPONSE TO OFFICE ACTION
Serial No. 10/624,763
Page 5 of 9

14. (Original) The method of claim 13 wherein step (b) further comprises:
- (b1) forming a photoresist pattern on the multilayer stack;
 - (b2) transferring the photoresist pattern through one or more layers of the multilayer stack; and
 - (b3) removing the photoresist pattern from the multilayer stack.
15. (Original) The method of claim 13 wherein the first mask comprises at least one of a dielectric antireflective coating (DARC) and an amorphous carbon layer.
16. (Currently Amended) The method of claim 13 wherein step (c) further comprises:
- (c1) depositing a second mask layer conformably on the first mask; and
 - (c2) etching portions of the second mask layer on horizontal surfaces of the substrate ~~leaving the second mask layer on one or more sidewalls of the first mask.~~
17. (Original) The method of claim 13 wherein the second mask comprises a material selected from the group consisting of silicon dioxide (SiO_2) and silicon nitride (Si_3N_4).
18. (Original) The method of claim 13 wherein the one or more material layers filling the notch gate opening formed in the multilayer stack comprise polysilicon.